



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

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In re the Application of: **HARADA, AKIHIKO et al**

Serial No.: **09/717,143**

Filed: **November 22, 2000**

For: **Insulated Gate Type Semiconductor Device and Method for Fabricating the Same**

MAY 21 2002
Group 1A Unit: 2826
MAIL ROOM

Examiner: **Ahmed Sefer**

AMENDMENT UNDER 37 CFR §1.111

Commissioner for Patents
Washington, D.C. 20231

May 20, 2002

Sir:

The response to the Office Action dated **December 19, 2001**, is requested to be extended to **May 19, 2002** by a 2 month Petition for Extension of Time. May 19, 2002 being a Sunday, this Amendment is filed on May 20, 2002, a Monday. Please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend the claims as follows:

Sub B
1. (Amended) An insulated gate type semiconductor device comprised of a semiconductor layer serving as an active region isolated from a semiconductor substrate by a substrate isolation insulating film, provided with a T-shaped gate electrode comprised of a trunk-shaped main gate electrode extending in parallel with respect to said semiconductor substrate, and a crosspiece-shaped conductor pattern extending in parallel with respect to said semiconductor substrate and also extending toward the width direction of said main gate electrode and having a length larger than the width of source and drain regions, and having a thickness of the gate insulating film formed directly